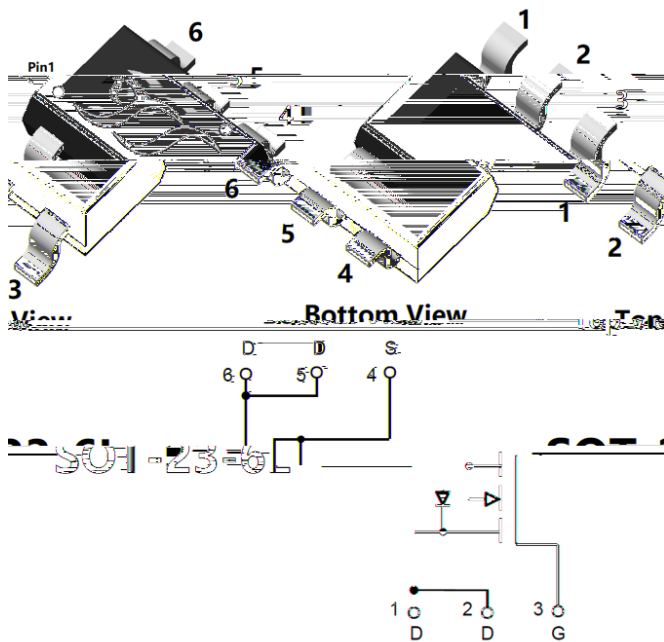




N-Channel Enhancement Mode Field Effect Transistor



Product Summary

DS	30V
D	5.6A
DS(ON)(at V _{GS} =10V)	25mohm
DS(ON)(at V _{GS} =4.5V)	31mohm
DS(ON)(at V _{GS} =2.5V)	45mohm
∇V _{DS} Tested	

General Description

Trench Power LV MOSFET technology
High density cell design for low R_{DS(ON)}
High Speed switching

Applications

Battery protection
Load switch
Power management

Absolute Maximum Ratings (T_A=25 unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V _{DS}	30	V
Gate-source Voltage		V _{GS}	± 12	V
Drain Current	T _A =25	I _D	5.6	A
	T _A =70		4.5	
Pulsed Drain Current ^A		I _{DM}	23	A
Total Power Dissipation	T _A =25	P _D	1.2	W
	T _A =70		0.8	W
Thermal Resistance Junction-to-Ambient ^B		R _{JA}	104	/W
Junction and Storage Temperature Range		T _J , T _{STG}	-55 +150	

Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJJ3400A	F2	3400A	3000	30000	120000	7"



YJJ3400A

RECOMMEND
YJJ3400B
FOR NEW DESIGN

Electrical Characteristics (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V			1	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =± 12V, V _{DS} =0V			± 100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =250	0.65	0.9	1.5	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =5.6A		20	25	m
		V _{GS} =4.5V, I _D =5A		23	31	
		V _{GS} =2.5V, I _D =3A		27	45	
Diode Forward Voltage	V _{SD}	I _S =5.6A, V _{GS} =0V			1.2	V
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, f=1MHz		630		pF
Output Capacitance	C _{oss}			55		
Reverse Transfer Capacitance	C _{rss}			71		
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =15V, I _D =5.6A		17.25		nC
Gate-Source Charge	Q _{gs}			2.1		
Gate-Drain Charge	Q _{gd}			2		
Reverse Recovery Charge	Q _{rr}	I _F =5.6A, di/dt=100A/us		1.1		
Reverse Recovery Time	t _{rr}			13.1		
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DS} =15V, I _D =5.6A R _{GEN} =		4.4		ns
Turn-on Rise Time	t _r			28.2		
Turn-off Delay Time	t _{D(off)}			16.2		
Turn-off fall Time	t _f			26		

A. Pulse Test: Pulse Width 300us, Duty cycle 2%.

B. R_{JA} is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{JC} is guaranteed by design, while R_{JA} is determined by the board design. The maximum rating presented here is based on mounting on a 1 in 2 pad of 2oz copper.



Typical Performance Characteristics

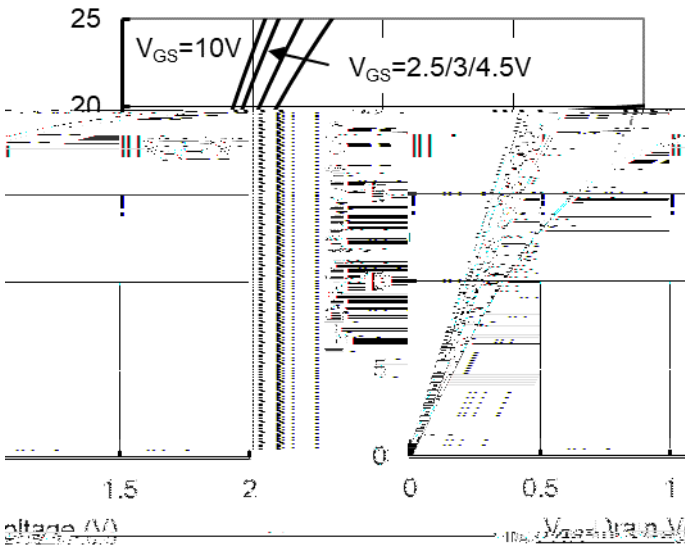


Figure1. Output Characteristics

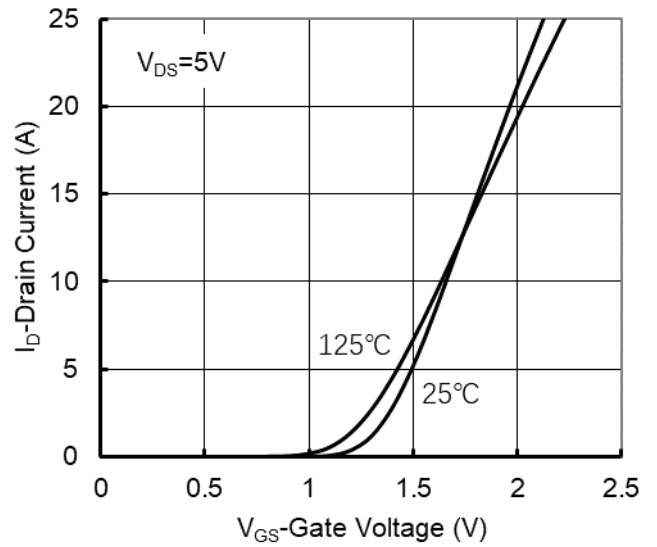


Figure2. Transfer Characteristics

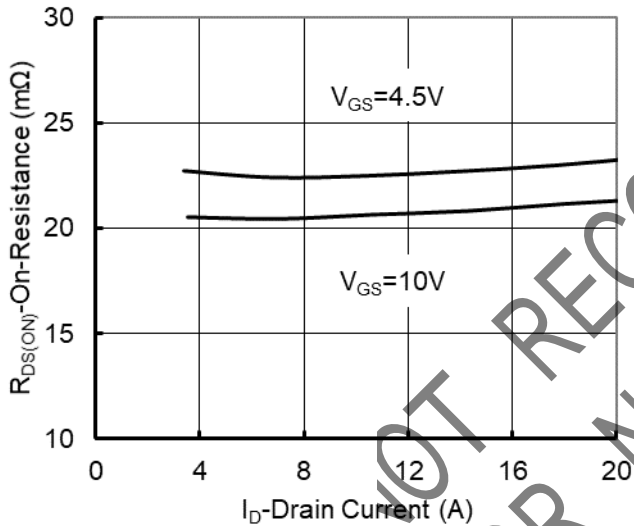


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

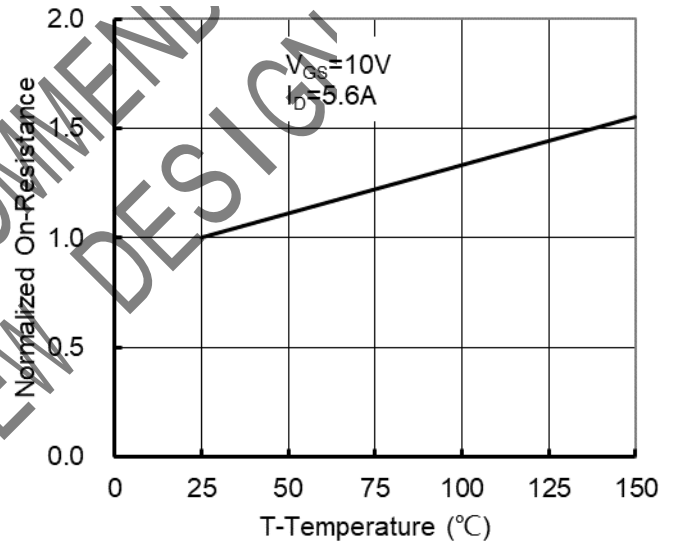


Figure 4: On-Resistance vs. Junction Temperature

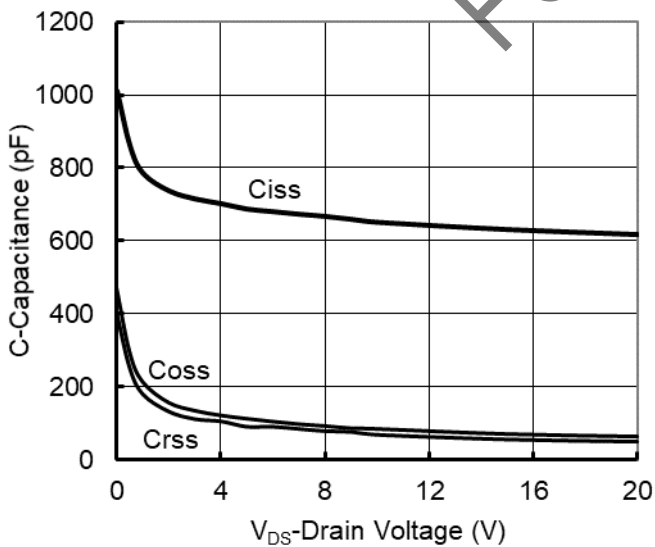


Figure5. Capacitance Characteristics

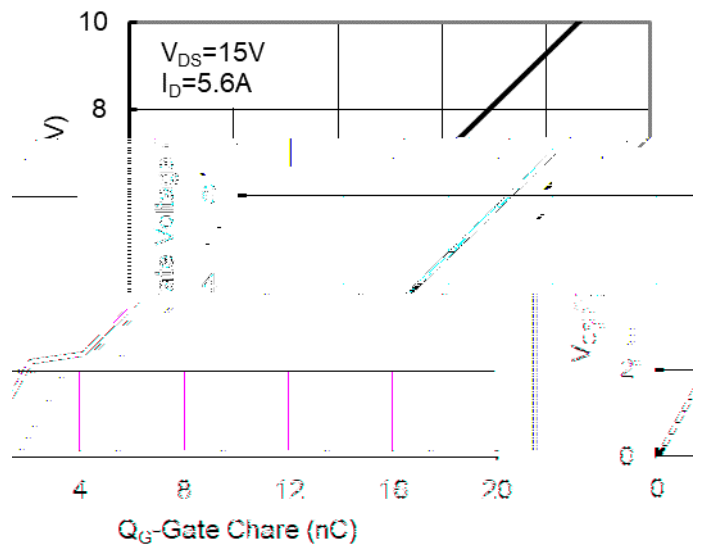


Figure6. Gate Charge

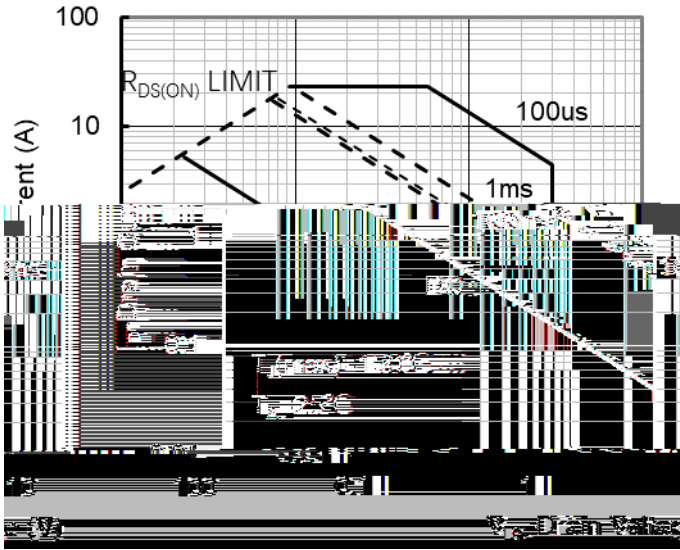


Figure7. Safe Operation Area

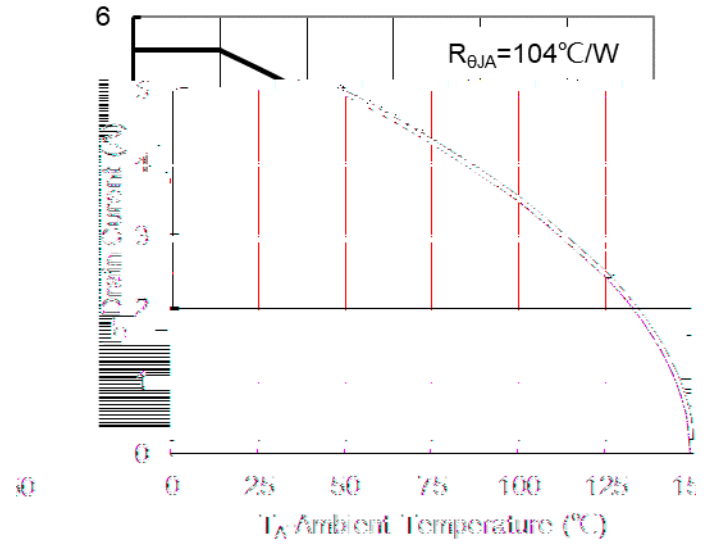


Figure8. Maximum Continuous Drain Current vs Ambient Temperature

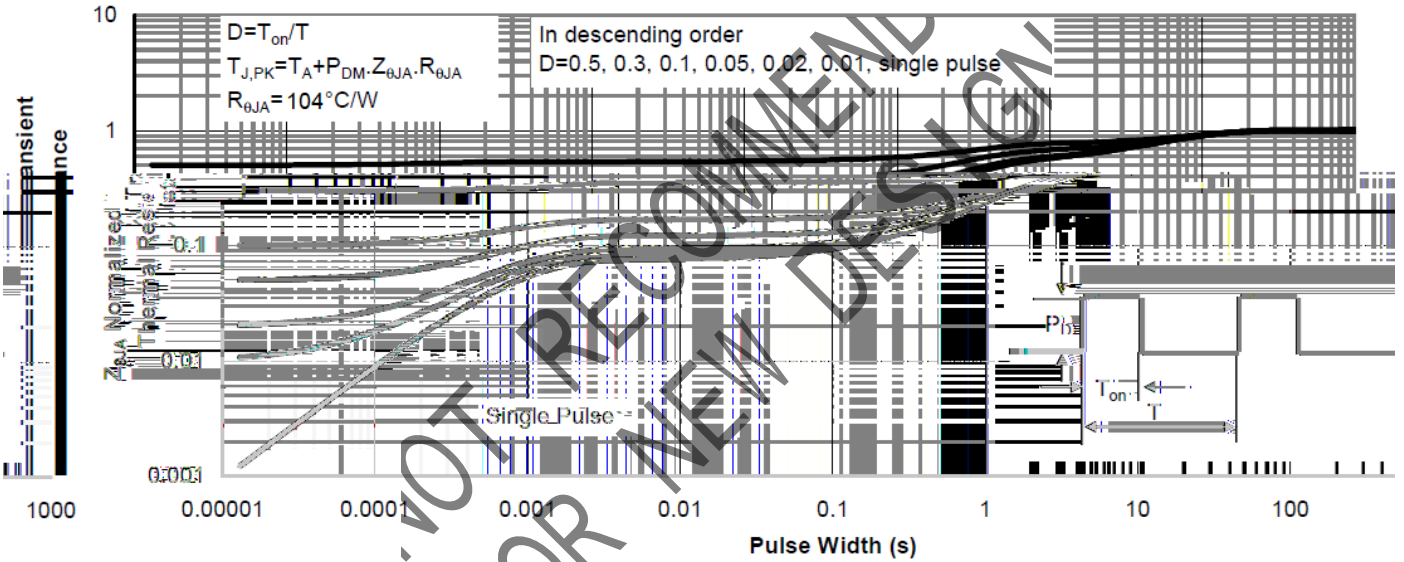
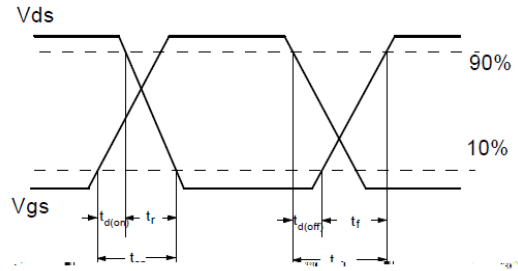
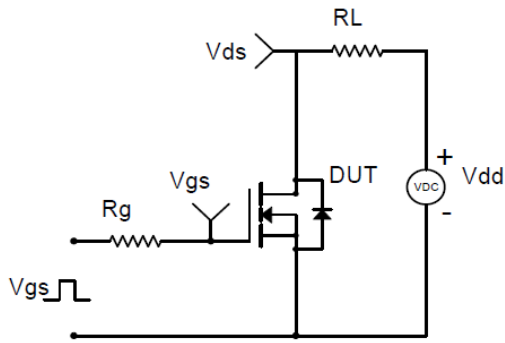
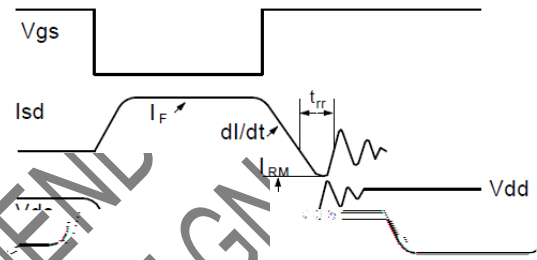
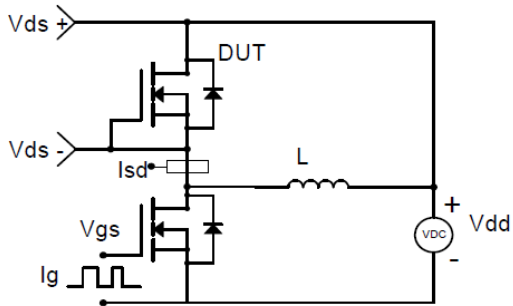


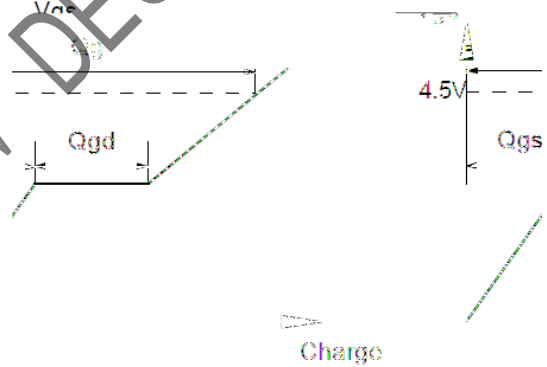
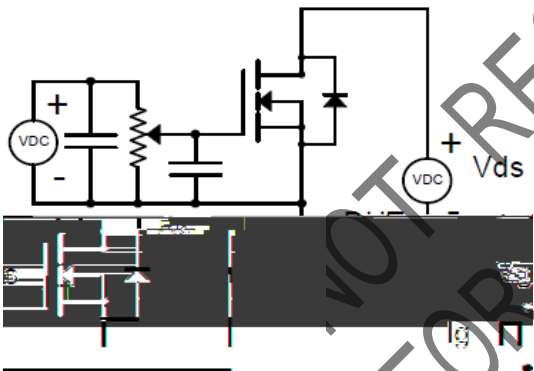
Figure9. Normalized Maximum Transient Thermal Impedance



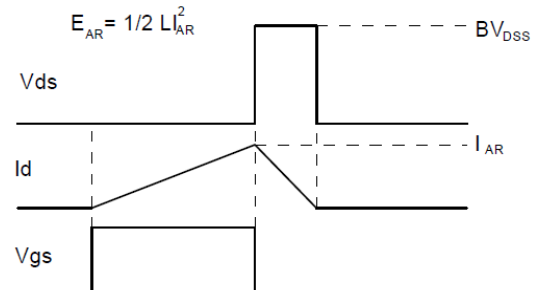
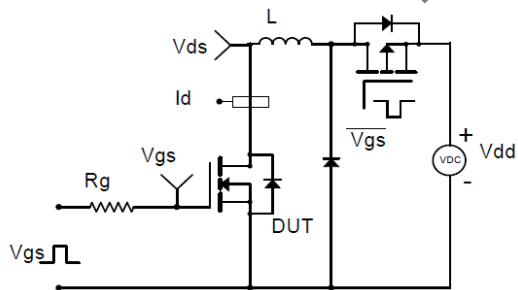
Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



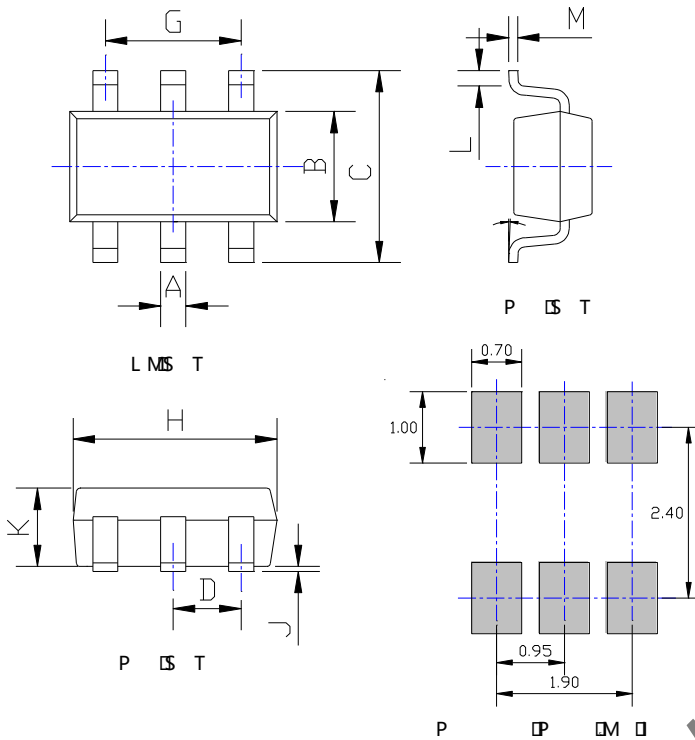
Gate Charge Test Circuit & Waveform



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



SOT-23-6L Package information



DIMENSIONS				
SYMBOL	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.012	0.020	0.300	0.500
B	0.059	0.067	1.500	1.700
C	0.104	0.116	2.650	2.950
D	0.037BSC		0.950BSC	
G	0.075BSC		1.900BSC	
H	0.111	0.119	2.820	3.020
J	0.000	0.004	0.000	0.100
K	0.041	0.045	1.050	1.150
L	0.012	0.024	0.300	0.600
M	0.004	0.008	0.100	0.200
	0°	8°	0°	8°

- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: $\pm 0.05\text{mm}$.
 3. The pad layout is for reference purposes only.

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